applying an upper interface wall on said insulator layer.

13. (Currently Amended) The method of claim 11, wherein said upper layer and ~~said~~ a bottom layer of said insulator layer ~~comprises~~ comprise silicon dioxide.

14. (Currently Amended) The method of claim 11, wherein ~~said~~ a middle layer of said insulator layer comprises silicon nitride.

15. (Original) The method of claim 11, wherein said step of creating voids in said insulator layer further comprises creating a plurality of voids from the upper layer of the insulator layer to an upper portion of the wiring layer.

16. (Original) The method of claim 11, wherein said fuse electrodes extend through said insulator layer to an underlying wiring layer.

17. (Original) The method of claim 16, wherein said fuse electrodes are diametrically opposed to one another.

18. (Currently Amended) The method in claim 16, wherein said fuse element is perpendicularly disposed above said ~~plurality of~~ fuse electrodes.

19. (Currently Amended) The method of claim 12, wherein said gap is confined by said ~~plurality of~~ fuse electrodes, said fuse element, and said middle layer of said insulator layer.

20. (Original) The method of claim 12, wherein said upper interface wall further comprises a first side wall, a second side wall, and an inner wall, wherein said inner wall is disposed within said gap.

21. (New) A method of producing a fuse structure, said method comprising:

applying an insulator layer over a wiring layer; wherein said insulator layer comprises an upper layer;

creating voids in said insulating layer and reducing a height of a fuse area of said upper layer between said voids;

filling said voids and said fuse with a fuse material to form fuse electrodes in said voids and a fuse element above said fuse area; and

removing said upper layer of said insulator layer, wherein said removing forms a gap between said fuse element and said insulator layer.

22. (New) The method of claim 21, further comprising

electroplating said fuse element; and

applying an upper interface wall on said insulator layer.

23. (New) The method of claim 21, wherein said upper layer and a bottom layer of said insulator layer comprise silicon dioxide.

24. (New) The method of claim 21, wherein a middle layer of said insulator layer comprises silicon nitride.

25. (New) The method of claim 21, wherein said step of creating voids in said insulator layer further comprises creating a plurality of voids from the upper layer of the insulator layer to an upper portion of the wiring layer.

26. (New) The method of claim 21, wherein said fuse electrodes extend through said insulator layer to an underlying wiring layer.

27. (New) The method of claim 26, wherein said fuse electrodes are diametrically opposed to one another.

28. (New) The method in claim 26, wherein said fuse element is perpendicularly disposed above said fuse electrodes.

29. (New) The method of claim 21, wherein said gap is confined by said fuse electrodes, said fuse element, and a middle layer of said insulator layer.

30. (New) The method of claim 22, wherein said upper interface wall further comprises a first side wall, a second side wall, and an inner wall, wherein said inner wall is disposed within said gap.